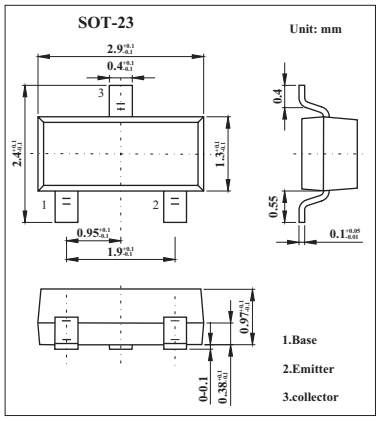
TY Semicondutor®

Product specification

2SC2463



■ Features

● Low frequency amplifier.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	55	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector dissipation	P_C	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = 10μA , I_E = 0	55			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1mA , R_{BE} = ∞	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E = 10μA , I_C = 0	5			V
Collector cutoff current	I_{CBO}	V_{CB} = 30V, I_E=0			0.5	μA
Emitter cutoff current	I_{EBO}	V_{EB} = 2V, I_C=0			0.5	μA
DC current gain	h_{FE}	V_{CE} = 12V , I_C = 2mA	250		1200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 10mA , I_B = 1mA			0.5	V
Base-emitter voltage	V_{BE}	V_{CE} = 12V , I_C = 2mA			0.75	V

■ h_{FE} Classification

Marking	DD	DE	DF
hFE	250～500	400～800	600～1200